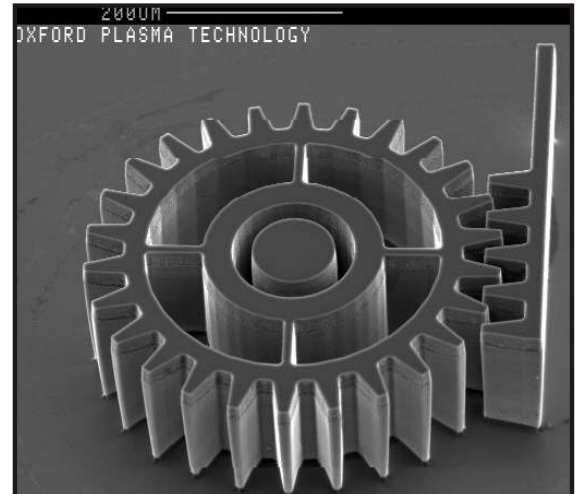
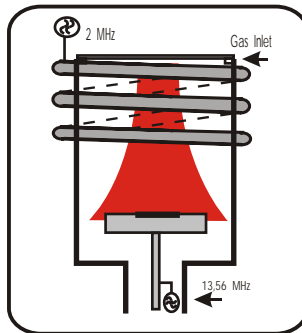
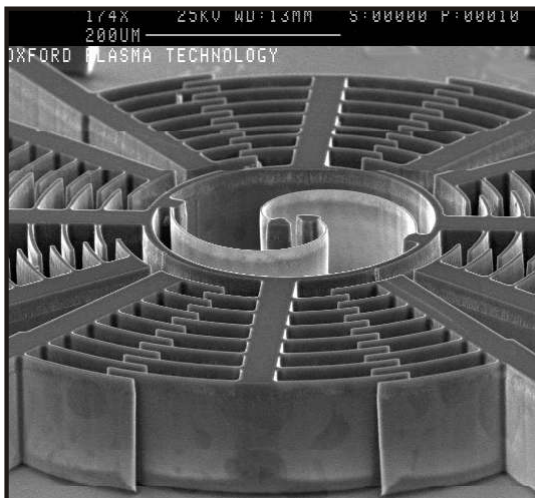
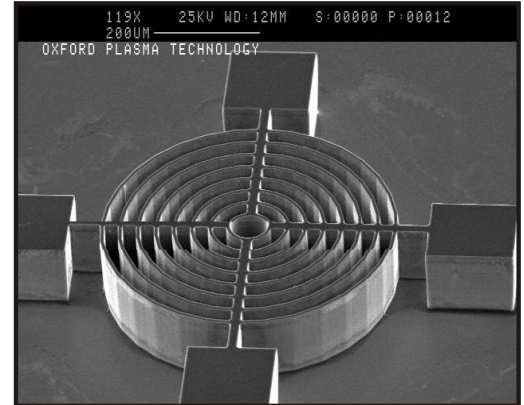
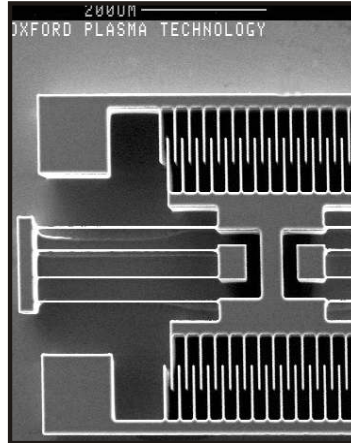
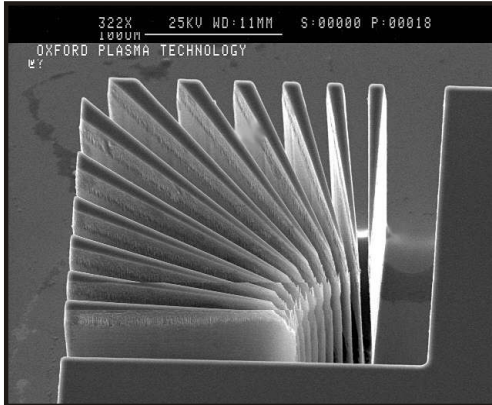


# Plasmalab Data

## Si etching for MEMS



etched at the OPT application lab, Yatton (UK)



### Technology:

Reactive Ion Etching  
Inductive Coupled Plasma Source  
room temperature process  
"Bosch process", gas chopping:  
isotropic etch/ polymer formation  
He backside cooling

### Results:

Rate : up to 10  $\mu\text{m}/\text{min}$   
Uniformity:  $\leq \pm 2/3\%$  (4/6")  
anisotropic etch  
aspect ratio up to 30 : 1  
controllable wall profile  
high selectivity to Resist (> 75:1)  
and  $\text{SiO}_2$  (>> 100:1)

## Plasmalab System 100